

NEC

DATA SHEET

NPN SILICON TRANSISTOR

2SC2570A

HIGH FREQUENCY LOW NOISE AMPLIFIER

NPN SILICON EPITAXIAL TRANSISTOR

DESCRIPTION

The 2SC2570A is designed for use in Low Noise Amplifier of VHF & UHF stages.

FEATURES

- Low noise and high gain : NF = 1.5 dB TYP., Ga = 8 dB TYP. @f = 1.0 GHz, V_{CE} = 10 V, I_C = 5.0 mA
- Wide dynamic range : NF = 1.9 dB, Ga = 9 dB @f = 1 GHz, V_{CE} = 10 V, I_C = 15 mA

ORDERING INFORMATION

Part Number	Quantity
2SC2570A	Loose products (500 pcs)
2SC2570A-T	Taping products (Box type) (2 500 pcs)

Remark To order evaluation samples, please contact your NEC sales office (available in 500-pcs units).

ABSOLUTE MAXIMUM RATINGS (T_A = +25 °C)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V _{CB0}	25	V
Collector to Emitter Voltage	V _{CE0}	12	V
Emitter to Base Voltage	V _{EB0}	3.0	V
Collector Current	I _C	70	mA
Total Power Dissipation	P _{tot}	600	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-65 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A = +25 °C)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
DC Current Gain	h _{FE} ^{Note 1}	V _{CE} = 10 V, I _C = 20 mA	40	–	200	–
Gain Bandwidth Product	f _r	V _{CE} = 10 V, I _C = 20 mA	–	5.0	–	GHz
Output Capacitance	C _{Ob} ^{Note 2}	V _{CB} = 10 V, I _E = 0, f = 1.0 MHz	–	0.7	0.9	pF
Insertion Power Gain	S _{21e} ²	V _{CE} = 10 V, I _C = 20 mA, f = 1.0 GHz	8	10	–	dB
Noise Figure	NF	V _{CE} = 10 V, I _C = 5 mA, f = 1.0 GHz	–	1.5	3.0	dB
Maximum Available Gain	MAG	V _{CE} = 10 V, I _C = 20 mA, f = 1.0 GHz	–	11.5	–	dB
Collector Cutoff Current	I _{CB0}	V _{CB} = 15 V, I _E = 0	–	–	0.1	μA
Emitter Cutoff Current	I _{EB0}	V _{EB} = 2.0 V, I _C = 0	–	–	0.1	μA

Notes 1. Pulse Measurement: PW ≤ 350 μs, Duty Cycle ≤ 2%

2. The emitter and case terminal should be connected to the guard terminal of the capacitance bridge.